

# Am29LV010B

1 Megabit (128 K x 8-Bit)

CMOS 3.0 Volt-only Uniform Sector Flash Memory

## DISTINCTIVE CHARACTERISTICS

### ■ Single power supply operation

- Full voltage range: 2.7 to 3.6 volt read and write operations for battery-powered applications
- Regulated voltage range: 3.0 to 3.6 volt read and write operations and for compatibility with high performance 3.3 volt microprocessors

### ■ Manufactured on 0.35 $\mu\text{m}$ process technology

### ■ High performance

- Full voltage range: access times as fast as 55 ns
- Regulated voltage range: access times as fast as 45 ns

### ■ Ultra low power consumption (typical values at 5 MHz)

- 200 nA Automatic Sleep mode current
- 200 nA standby mode current
- 7 mA read current
- 15 mA program/erase current

### ■ Flexible sector architecture

- Eight 16 Kbyte
- Supports full chip erase
- Sector Protection features:
  - Hardware method of locking a sector to prevent any program or erase operations within that sector
  - Sectors can be locked in-system or via programming equipment
  - Temporary Sector Unprotect feature allows code changes in previously locked sectors

### ■ Unlock Bypass Mode Program Command

- Reduces overall programming time when issuing multiple program command sequences

### ■ Embedded Algorithms

- Embedded Erase algorithm automatically preprograms and erases the entire chip or any combination of designated sectors
- Embedded Program algorithm automatically writes and verifies data at specified addresses

### ■ Minimum 1,000,000 write cycle guarantee per sector

### ■ Package option

- 32-pin TSOP
- 32-pin PLCC

### ■ Compatibility with JEDEC standards

- Pinout and software compatible with single-power supply Flash
- Superior inadvertent write protection

### ■ Data# Polling and toggle bits

- Provides a software method of detecting program or erase operation completion

### ■ Erase Suspend/Erase Resume

- Supports reading data from or programming data to a sector that is not being erased

## GENERAL DESCRIPTION

The Am29LV010B is a 1 Mbit, 3.0 Volt-only Flash memory device organized as 131,072 bytes. The Am29LV010B has a uniform sector architecture.

The device is offered in 32-pin PLCC and 32-pin TSOP packages. The byte-wide (x8) data appears on DQ7–DQ0. All read, erase, and program operations are accomplished using only a single power supply. The device can also be programmed in standard EPROM programmers.

The standard Am29LV010B offers access times of 45, 55, 70, and 120 ns (90 and 100 ns parts are also available), allowing high speed microprocessors to operate without wait states. To eliminate bus contention, the device has separate chip enable (CE#), write enable (WE#) and output enable (OE#) controls.

The device requires only a **single power supply** (2.7 V–3.6V) for both read and write functions. Internally generated and regulated voltages are provided for the program and erase operations.

The device is entirely command set compatible with the **JEDEC single-power-supply Flash standard**. Commands are written to the command register using standard microprocessor write timings. Register contents serve as input to an internal state-machine that controls the erase and programming circuitry. Write cycles also internally latch addresses and data needed for the programming and erase operations. Reading data out of the device is similar to reading from other Flash or EPROM devices.

Device programming occurs by executing the program command sequence. This initiates the **Embedded Program** algorithm—an internal algorithm that automatically times the program pulse widths and verifies proper cell margin. The **Unlock Bypass** mode facilitates faster programming times by requiring only two write cycles to program data instead of four.

Device erasure occurs by executing the erase command sequence. This initiates the **Embedded Erase**

algorithm—an internal algorithm that automatically preprograms the array (if it is not already programmed) before executing the erase operation. During erase, the device automatically times the erase pulse widths and verifies proper cell margin.

The host system can detect whether a program or erase operation is complete by reading the DQ7 (Data# Polling) and DQ6 (toggle) **status bits**. After a program or erase cycle has been completed, the device is ready to read array data or accept another command.

The **sector erase architecture** allows memory sectors to be erased and reprogrammed without affecting the data contents of other sectors. The device is fully erased when shipped from the factory.

**Hardware data protection** measures include a low  $V_{CC}$  detector that automatically inhibits write operations during power transitions. The **hardware sector protection** feature disables both program and erase operations in any combination of the sectors of memory. This can be achieved in-system or via programming equipment.

The **Erase Suspend** feature enables the user to put erase on hold for any period of time to read data from, or program data to, any sector that is not selected for erasure. True background erase can thus be achieved.

The device offers two power-saving features. When addresses have been stable for a specified amount of time, the device enters the **automatic sleep mode**. The system can also place the device into the **standby mode**. Power consumption is greatly reduced in both these modes.

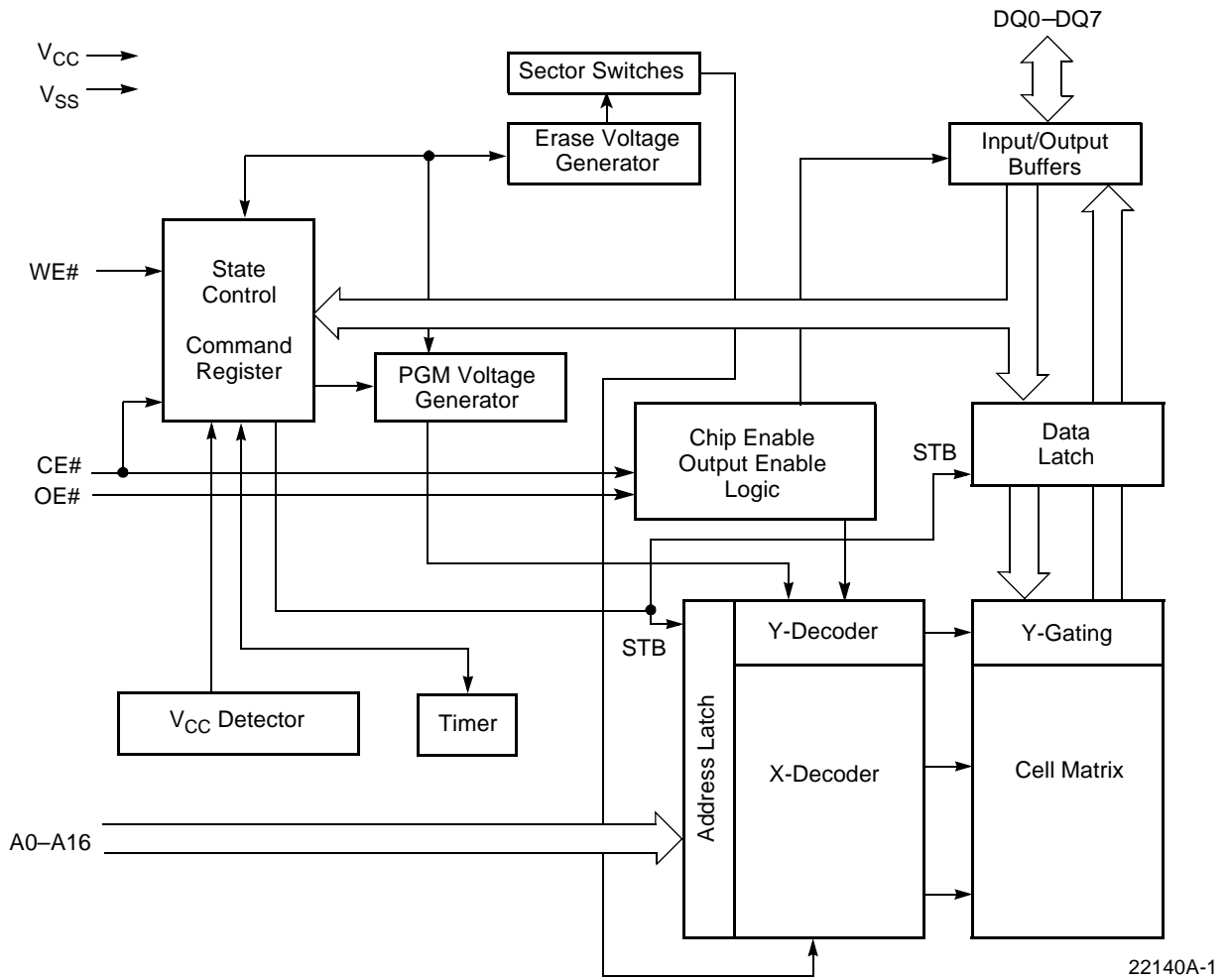
AMD's Flash technology combines years of Flash memory manufacturing experience to produce the highest levels of quality, reliability and cost effectiveness. The device electrically erases all bits within a sector simultaneously via Fowler-Nordheim tunneling. The data is programmed using hot electron injection.

PRODUCT SELECTOR GUIDE

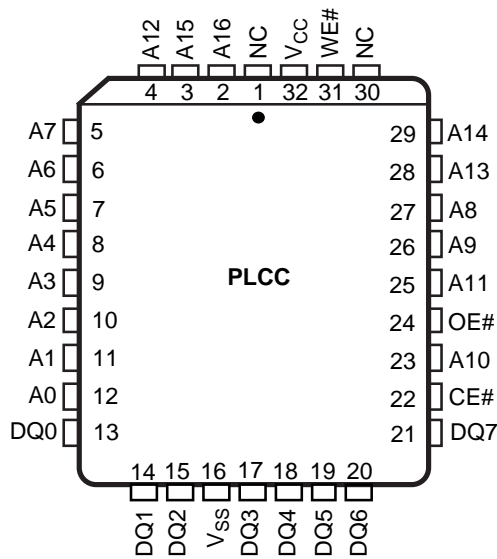
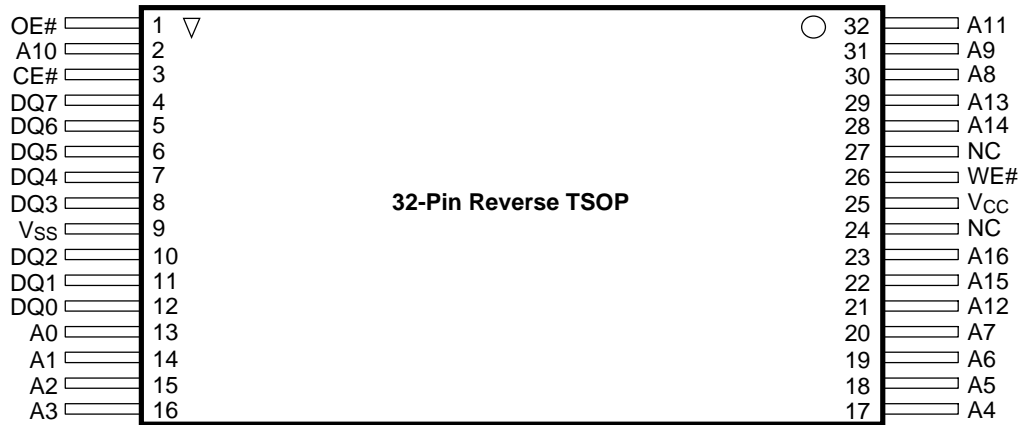
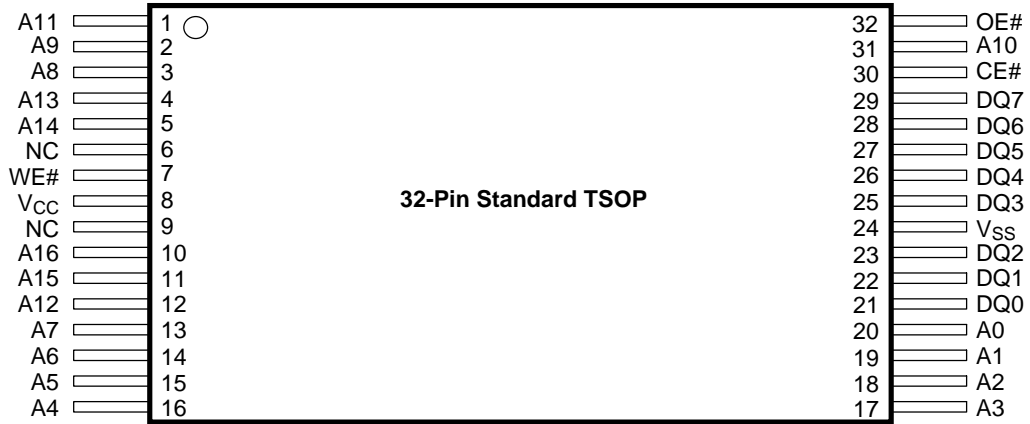
| Family Part Number                   |  | Am29LV010B |     |     |      |
|--------------------------------------|--|------------|-----|-----|------|
| Speed Options                        | Regulated Voltage Range: $V_{CC} = 3.0-3.6\text{ V}$ | -45R       |     |     |      |
|                                      | Full Voltage Range: $V_{CC} = 2.7-3.6\text{ V}$      |            | -55 | -70 | -120 |
| Max access time, ns ( $t_{ACC}$ )    |  | 45         | 55  | 70  | 120  |
| Max CE# access time, ns ( $t_{CE}$ ) |  | 45         | 55  | 70  | 120  |
| Max OE# access time, ns ( $t_{OE}$ ) |  | 30         | 30  | 35  | 50   |

Note: See "AC Characteristics" for full specifications.

BLOCK DIAGRAM



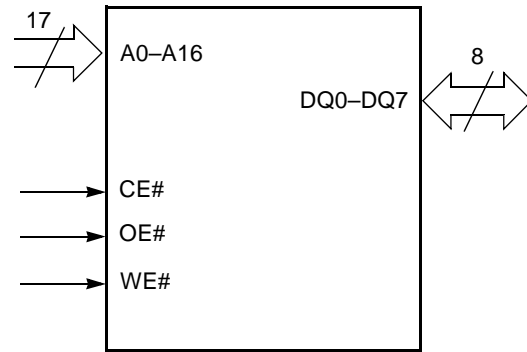
CONNECTION DIAGRAMS



**PIN CONFIGURATION**

- A0–A16 = 17 addresses
- DQ0–DQ7 = 8 data inputs/outputs
- CE# = Chip enable
- OE# = Output enable
- WE# = Write enable
- V<sub>CC</sub> = 3.0 volt-only single power supply  
(see Product Selector Guide for speed options and voltage supply tolerances)
- V<sub>SS</sub> = Device ground
- NC = Pin not connected internally

**LOGIC SYMBOL**

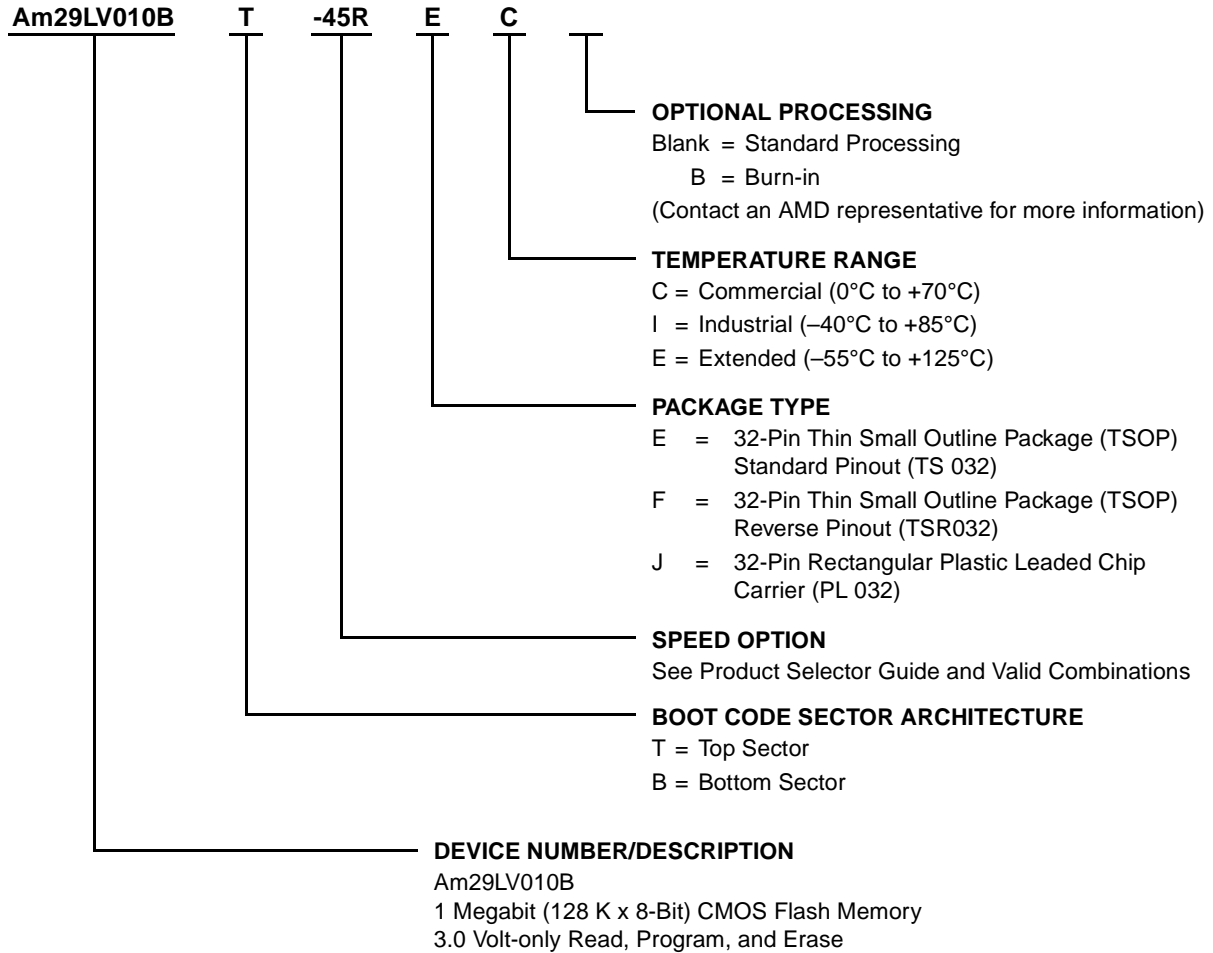


22140A-3

**ORDERING INFORMATION**

**Standard Products**

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of the elements below.



| Valid Combinations |  |
|--------------------|--|
| Am29LV010B-45R     | EC, FC, JC                               |
| Am29LV010B-55      | EC, EI, EE,<br>FC, FI, FE,<br>JC, JI, JE |
| Am29LV010B-70      |  |
| Am29LV010B-120     |  |

**Valid Combinations**

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations and to check on newly released combinations.

**REVISION SUMMARY****Revision A**

Split the Am29LV001B/Am29LV010B data sheet into separate documents. The Am29LV001B data sheet retains publication number 21557B and later; the Am29LV010B data sheet has been reassigned publication number 22140.

**Valid Combinations**

Changes since publication number 21557A was released: deleted the "R" designation from the 55 ns option. Corrected the part numbers.

**Trademarks**

Copyright © 1998 Advanced Micro Devices, Inc. All rights reserved.

AMD, the AMD logo, and combinations thereof are registered trademarks of Advanced Micro Devices, Inc.

Product names used in this publication are for identification purposes only and may be trademarks of their respective companies.